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INTEGRATED CIRCUIT WITH SELF-ALIGNED LINE AND VIA AND MANUFACTURING METHOD THEREFOR

ABSTRACT

An integrated circuit and manufacturing method therefor is provided having a base with a first dielectric layer formed thereon. A second dielectric layer is formed over the first dielectric layer. A third dielectric layer is formed in spaced-apart strips over the second dielectric layer. A first trench opening is formed through the first and second dielectric layers between the spaced-apart strips of the third dielectric layer. A second trench opening is formed contiguously with the first trench opening through the first dielectric layer between the spaced-apart strips of the third dielectric layer. Conductor metals in the trench openings form self-aligned trench interconnects.

FIGURE 1